

BUK9620-55A

N-channel TrenchMOS logic level FET Rev. 02 — 4 June 2010

Product data sheet

Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Motors, lamps and solenoids

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	54	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	118	W
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	-	21	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	15	18	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	17	20	mΩ
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 48 \text{ A; } V_{sup} \leq 55 \text{ V;} \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	115	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9620-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _i ≥ 25 °C; T _i ≤ 175 °C	-	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	-	55	V
V _{GS}	gate-source voltage		-10	-	10	V
I _D	drain current	$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	-	-	38	Α
		$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 5 \text{V};$ see Figure 1; see Figure 3	-	-	54	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; t_p ≤ 10 μs; pulsed; see Figure 3	-	-	217	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	118	W
T _{stg}	storage temperature		-55	-	175	°C
Tj	junction temperature		-55	-	175	°C
V_{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \mu s$	-15	-	15	V
Source-drai	n diode					
Is	source current	T _{mb} = 25 °C	-	-	54	Α
I _{SM}	peak source current	$t_p = 10 \mu s$; pulsed; $T_{mb} = 25 ^{\circ}C$	-	-	217	Α
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 48 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	115	mJ

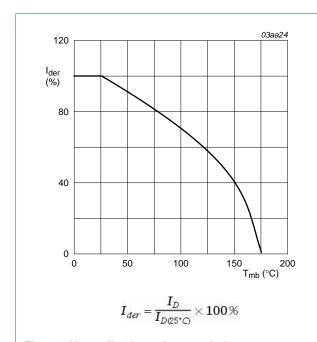


Fig 1. Normalized continuous drain current as a function of mounting base temperature

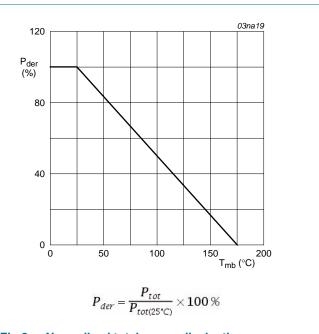
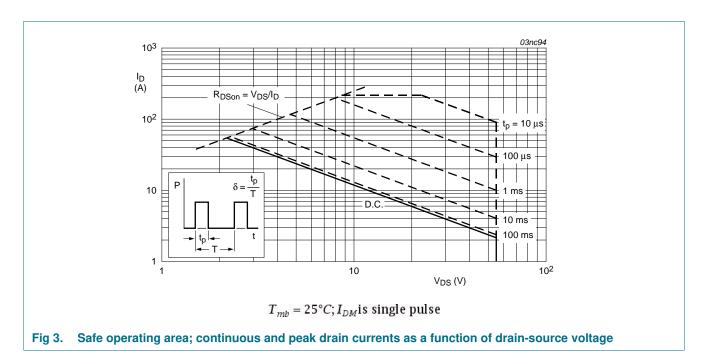


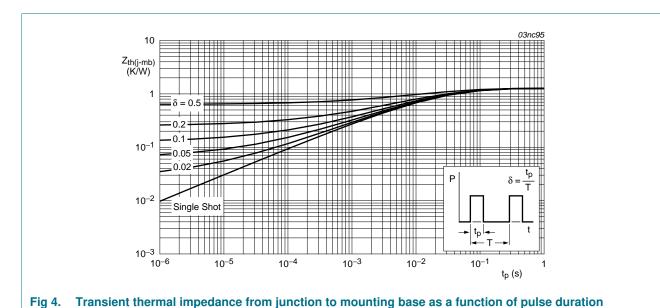
Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board; SOT404 package; minimum footprint	-	50	-	K/W



BUK9620-55A

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u>	1	1.5	2	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 11</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	21	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	40	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	15	18	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	17	20	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1660	2210	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	290	346	рF
C_{rss}	reverse transfer capacitance		-	194	266	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	19	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 \degree C$	-	124	-	ns
t _{d(off)}	turn-off delay time		-	92	-	ns
t _f	fall time		-	93	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25$ °C	-	4.5	-	nΗ
		from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	52	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	81	-	nC

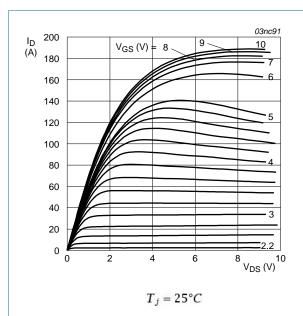


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

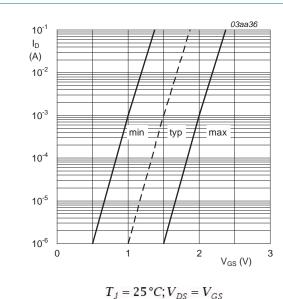
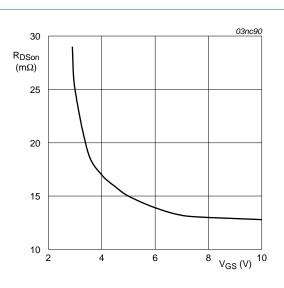
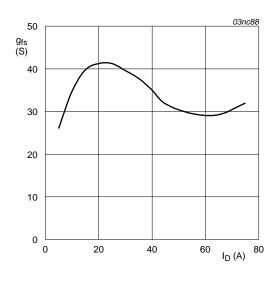


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25^{\circ}C; V_{DS} = 25V$

Fig 8. Forward transconductance as a function of drain current; typical values

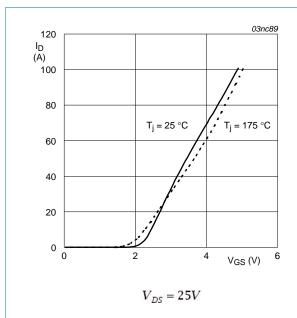


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

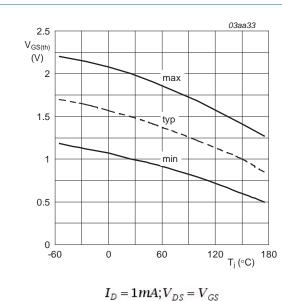
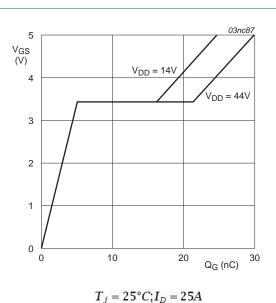


Fig 11. Gate-source threshold voltage as a function of junction temperature



J

Fig 10. Gate-source voltage as a function of gate charge; typical values

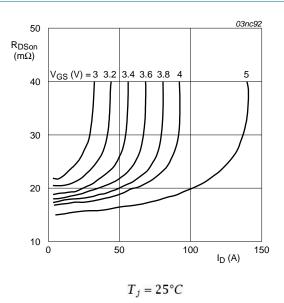


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

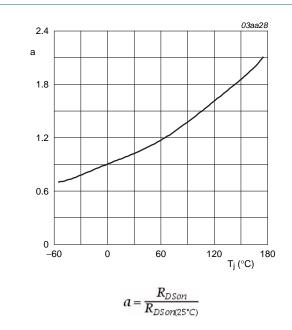
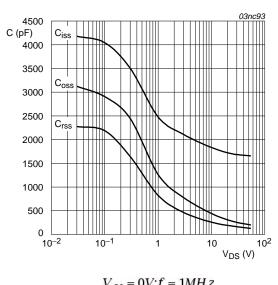


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

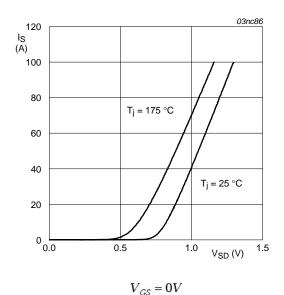


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

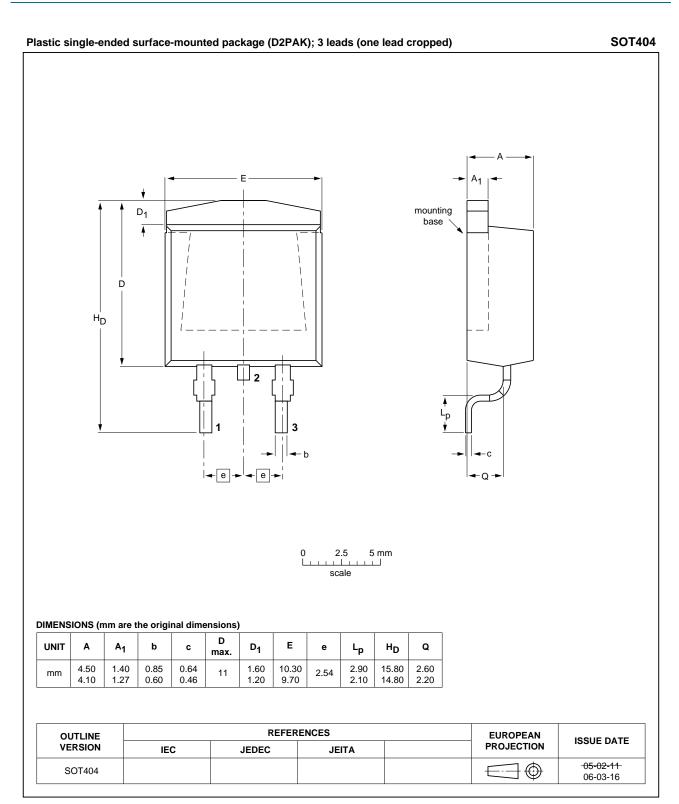


Fig 16. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9620-55A v.2	20100604	Product data sheet	-	BUK9520_9620_55A-01
Modifications: • The format of this data sheet has been redesigned to comply with the new ide of NXP Semiconductors.				the new identity guidelines
	 Legal texts l 	have been adapted to the r	new company name where	appropriate.
	 Type number 	er BUK9620-55A separated	from data sheet BUK9520)_9620_55A-01.
BUK9520_9620_55A-01 (9397 750 07794)	20010129	Product Specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel TrenchMOS logic level FET

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